

CoventorWare® 10 Overview

노 용 주
(주)이디앤씨

June, 2015

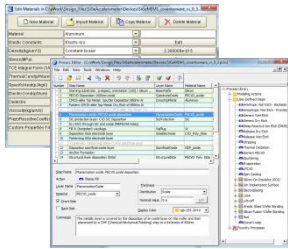
Distributed and supported by ED&C

CoventorWare, from 2D Layout to 3D Simulations

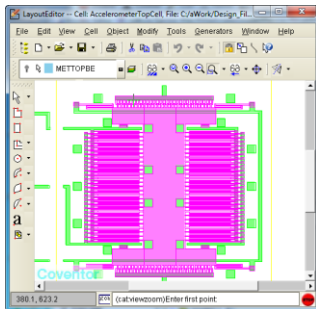
COVENTOR

DESIGNER

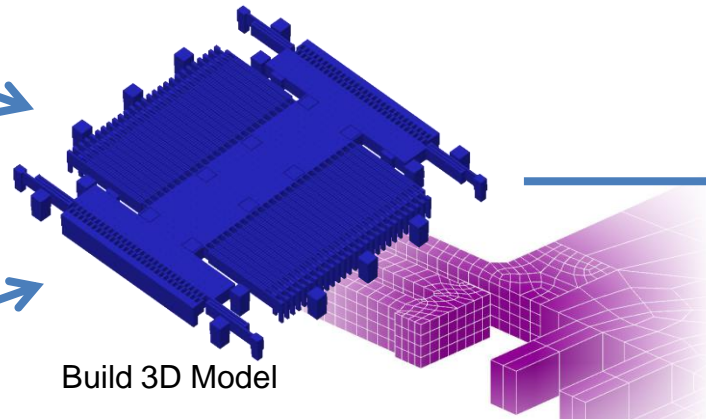
ANALYZER



Materials & Process

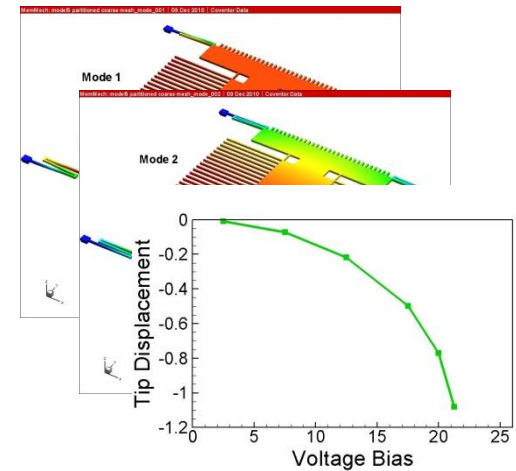


Create 2D Layout



Build 3D Model

Automatically
Generate Mesh



Simulate, Visualize, and Analyze

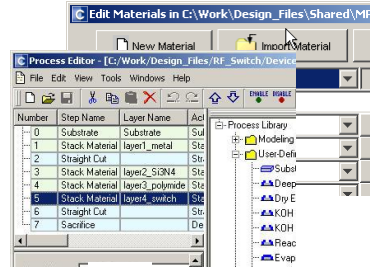
Process-Centric
Design Entry

Preprocessing and Mesh Generation
Optimized for MEMS Geometry

Hybrid FEM/BEM Suite
of Multi-Physics Field Solvers

Materials & Process

Customizable for any MEMS process

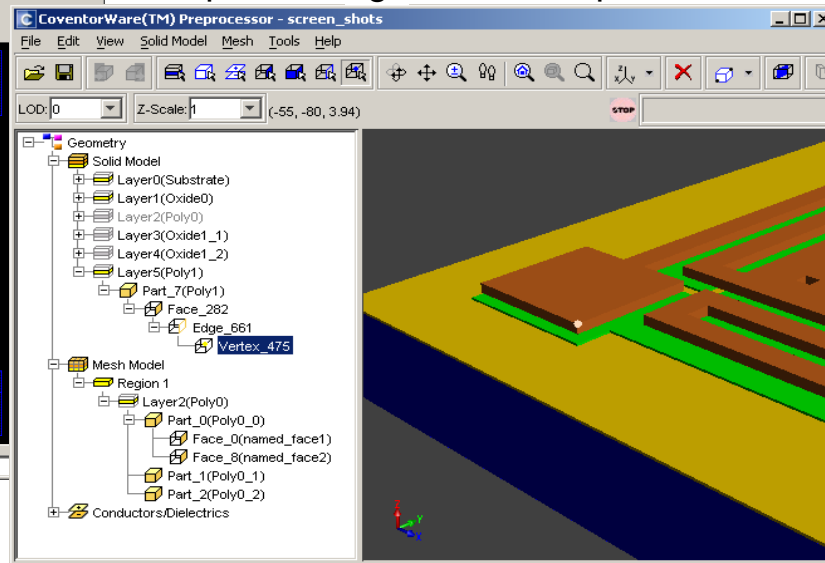
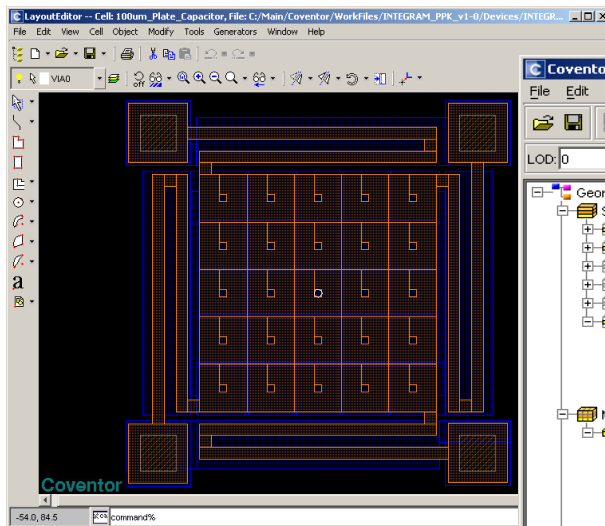


2D Layout Editor

with MEMS-specific features

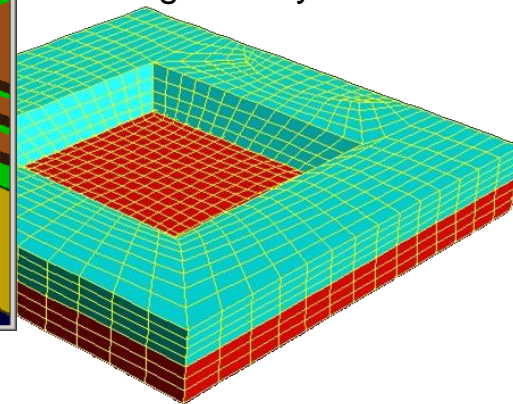
Preprocessor

with partitioning, transform operations,...



Automatic Meshing

meshers optimized for MEMS geometry



DESIGNER Process Editor

COVENTOR

Descriptive
step names

Customizable
step hierarchy

User customizable
library of standard
process steps
(mapped to solid
modeling steps)

Access to standard
foundry processes

Number	Step Name	Action	Layer Name	Material Name	Thickness
1	Substrate	SubstrateStep	Substrate	SILICON	10
2	MetalMUMPs	Sequence			
2.1	KOH Wet Etch	StraightCutStep			
2.2	Thermal Oxidation	StackMaterialStep	IsolationOxide	THERM_OXIDE	2
2.3	Release HF Etch	StraightCutStep	<choose>		
2.4	PDG Deposition Part 1	PlanarFillStep	EtchedIsolationOxide	PSG	0
2.5	PDG Deposition Part 2	StackMaterialStep	Oxide1	PSG	0.5
2.6	Wet Etch	StraightCutStep	<choose>		
2.7	LPCVD	ConformalShellStep	Nitride1	SiNxNy_MetalMUMPs	0.35
2.8	RIE Etch	StraightCutStep	<choose>		
2.9	LPCVD	ConformalShellStep	Poly	POLYSILICON_MetalMUMPs	0.7
2.10	RIE Etch	StraightCutStep	<choose>		
2.11	RIE Etch	StraightCutStep	<choose>		
2.12	LPCVD	ConformalShellStep	Nitride2	SiNxNy_MetalMUMPs	0.35
2.13	RIE Etch	StraightCutStep	<choose>		
2.14	PDG Deposition	ConformalShellStep	Oxide2	PSG	1.1
2.15	Wet Etch	StraightCutStep	<choose>		

Step Name: KOH Wet Etch
Action: Straight Cut

Cut Layer: <choose>
 Depth: Distribution: Scalar, Nominal Value: 25
 Front Side
 Back Side

Mask: Oxide1
Photoresist: -
Sidewall Angle(degrees): Distribution: Scalar, Nominal Value: -35.3
Offset: Distribution: Scalar, Nominal Value: 0

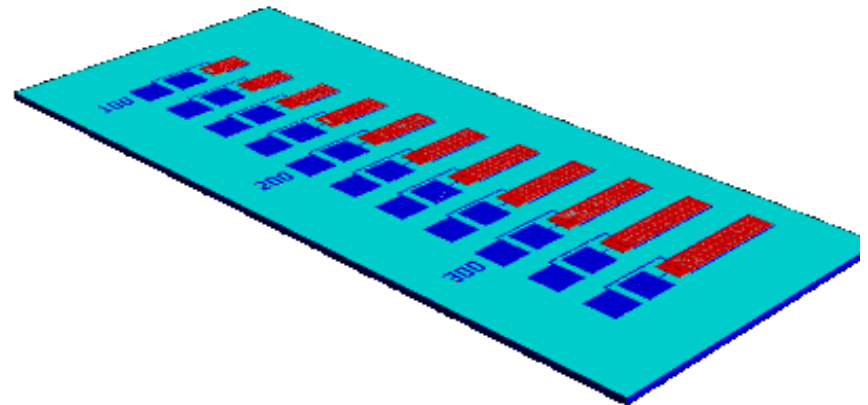
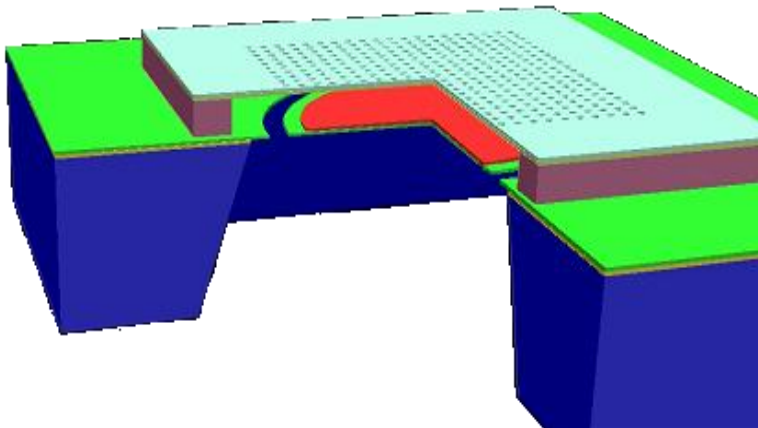
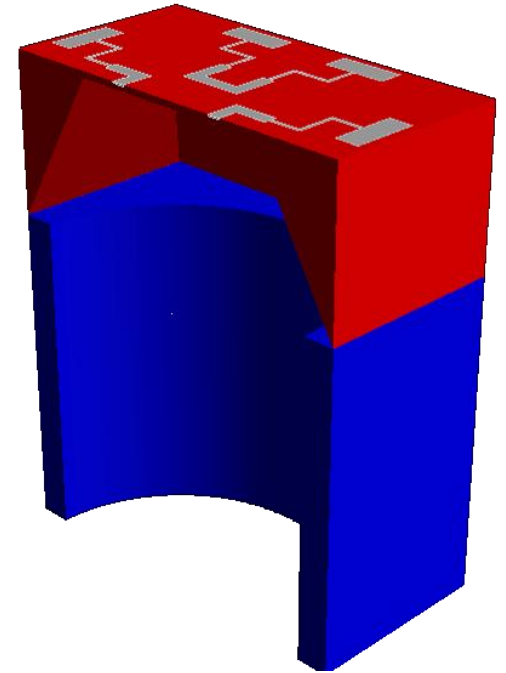
Comments: KOH silicon etch is used to form a 25µm deep trench in the silicon substrate in the areas defined by the OXIDE1 and NITRHOLE mask levels.

- Process Steps
 - Anodic Glass Wafer Bonding
 - Deep Reactive Ion Etch (DRIE)
 - Dry Etch
 - Electroplating
 - Electroplating simplified
 - Epi- SOI (Silicon-On-Insulator)
 - Evaporation
 - Ion Implantation
 - KOH Wet Etch - Backside
 - KOH Wet Etch - Frontside
 - Lift-off
 - LIGA
 - LPCVD
 - LPCVD simplified
 - PECVD
 - PECVD simplified
 - Reactive Ion Etch (RIE)
 - Release Dry Etch
 - Release HF Etch
 - Release Wet Etch
 - Silicon Fusion Wafer Bonding
 - Silicon-On-Insulator (SOI)
 - Spin Casting
 - Sputtering
 - Stripping
 - Substrate
 - Thermal Oxidation
 - Thermal Oxidation simplified
- Modeling Steps
- Pre CoventorWare 2005 Steps
- Foundry Processes
 - MetalMUMPs
 - PolyMUMPs

DESIGNER Solid Modeler

COVENTOR

- Employs the 2D layout and fabrication process description to automatically build 3D models (ACIS SAT format)
- Emulates real foundry steps, such as etching through multiple layers or partial backside etching



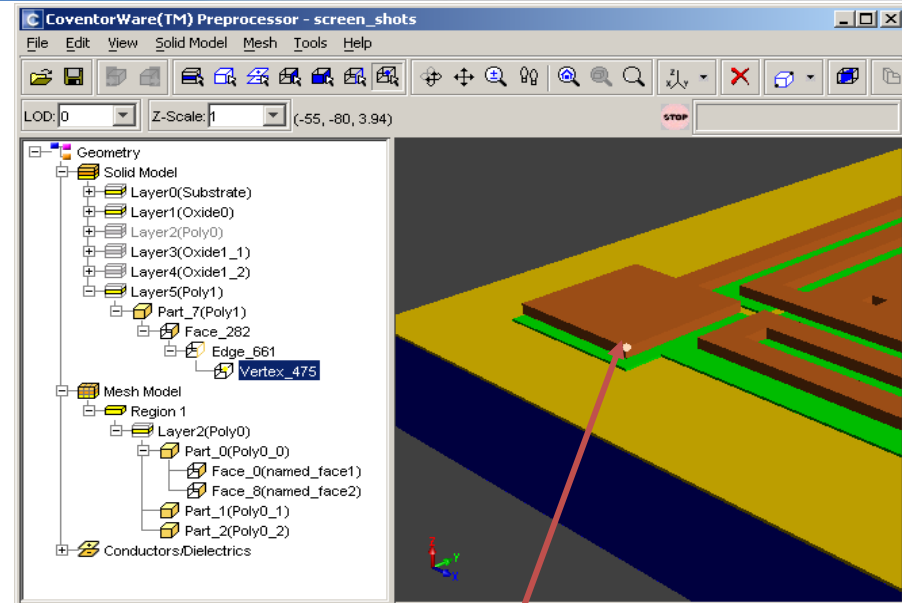
DESIGNER -- ANALYZER Preprocessor

COVENTOR

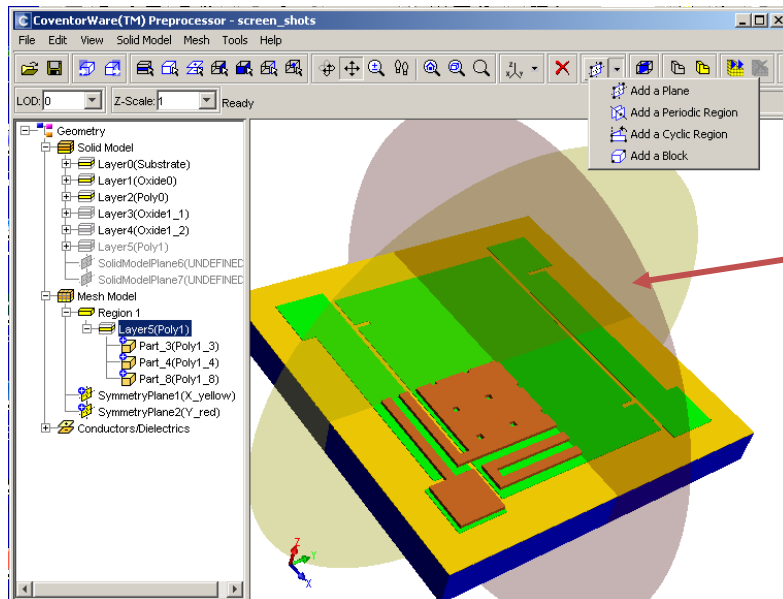
Optimized for MEMs layers

Features include

- Cross-section planes
- Solid model partitioning & transforms
- Automatic layer merging to assure conformal meshes
- Part and face labeling for BCs
- Mesh generation
- Mesh quality checks



Tree expands to show only named or highlighted entities



Same plane can be used as x-section, partition or symmetry.

DESIGNER -- ANALYZER

Meshing

COVENTOR

Choose from 5 optimized mesh generators that are ideal for MEMS solid models

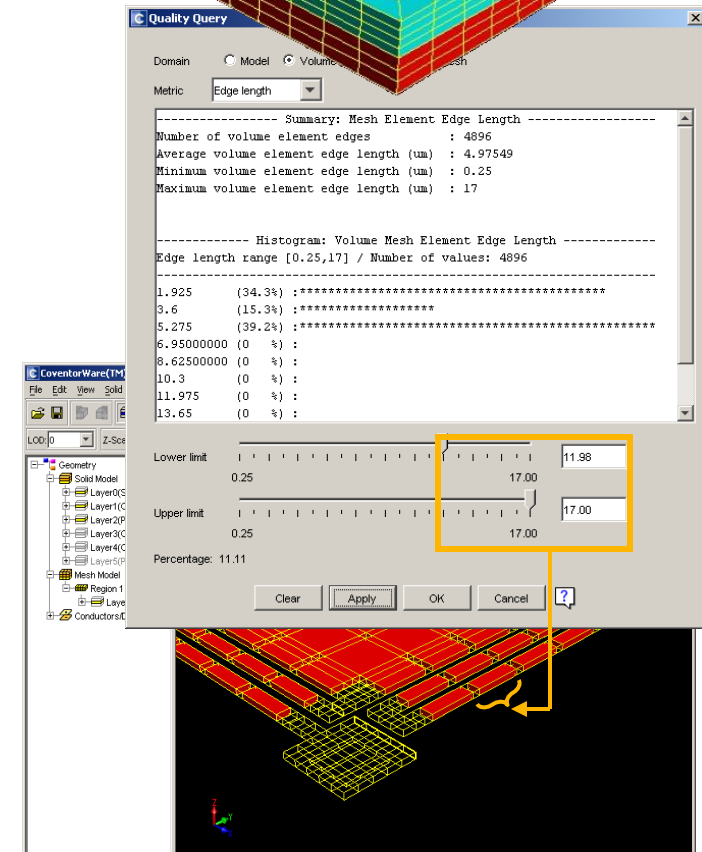
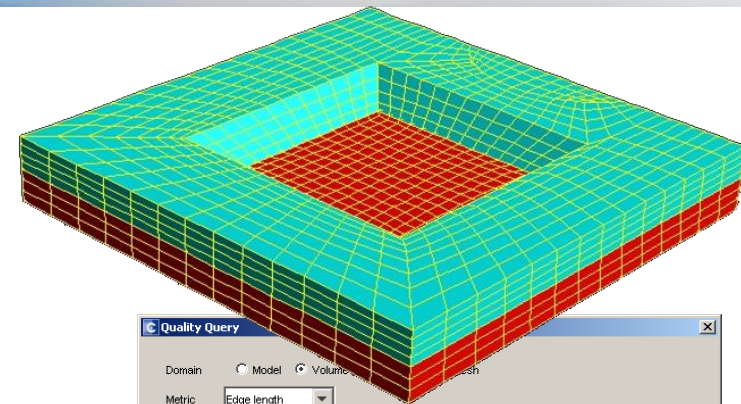
1. Manhattan bricks (hexes) for near orthogonal geometry
2. Extruded bricks for multi-layered non-orthogonal geometry (choose from 3 algorithms)
3. Mapped meshing for 6-sided volumes
4. Tetrahedral meshing for arbitrary shapes
5. Surface meshing (triangles and quadrilaterals) for BEM

Local refinement controls on all model entities (layers, parts, faces, edges, vertices)

Mesh quality checks

- Easy to read reports
- Highlighted display of “bad” elements

Import/export ANSYS meshes



Quality Query

Domain: Model Volume

Metric: Edge length

Summary: Mesh Element Edge Length

Number of volume element edges	: 4896
Average volume element edge length (um)	: 4.97549
Minimum volume element edge length (um)	: 0.25
Maximum volume element edge length (um)	: 17

Histogram: Volume Mesh Element Edge Length

Edge length range [0.25,17] / Number of values: 4896

1.925	(34.3%)	*****
3.6	(15.3%)	*****
5.275	(39.2%)	*****
6.95000000	(0 %)	:
8.62500000	(0 %)	:
10.3	(0 %)	:
11.975	(0 %)	:
13.65	(0 %)	:

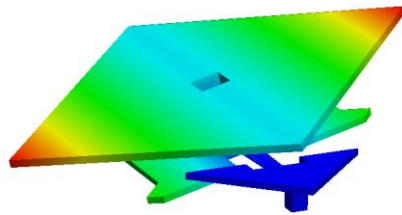
Lower limit: 0.25 | 17.00 | 11.98

Upper limit: 0.25 | 17.00

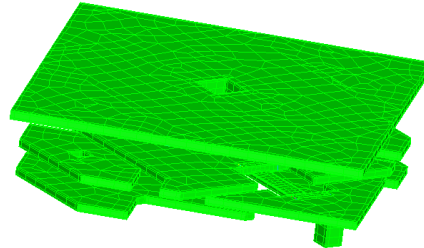
Percentage: 11.11

Buttons: Clear, Apply, OK, Cancel

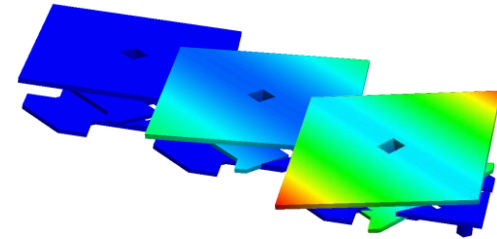
World-class coupled electro-mechanics simulations



Finite element (FEM)
non-linear **mechanics**

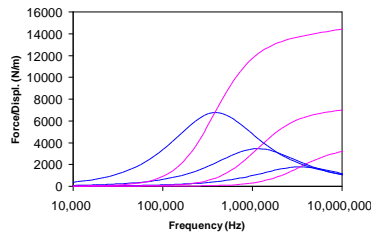


Boundary element (BEM)
electrostatics – no need to mesh air

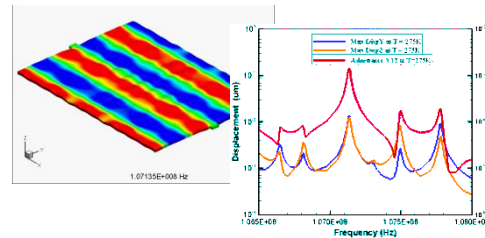


Hybrid FEM/BEM **pull-in/lift-off**

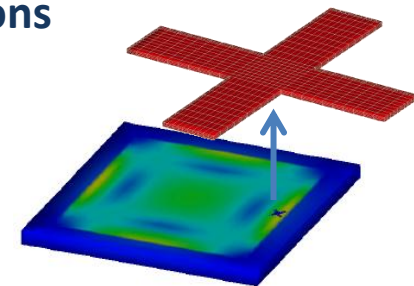
Specialty MEMS physics simulations



Reynolds and Stokes
solvers for **gas damping**



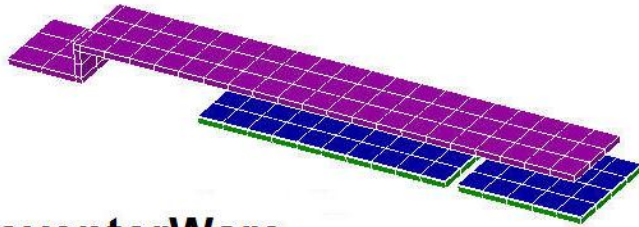
Fast modal harmonic analysis
for **piezo (PZE) resonators**



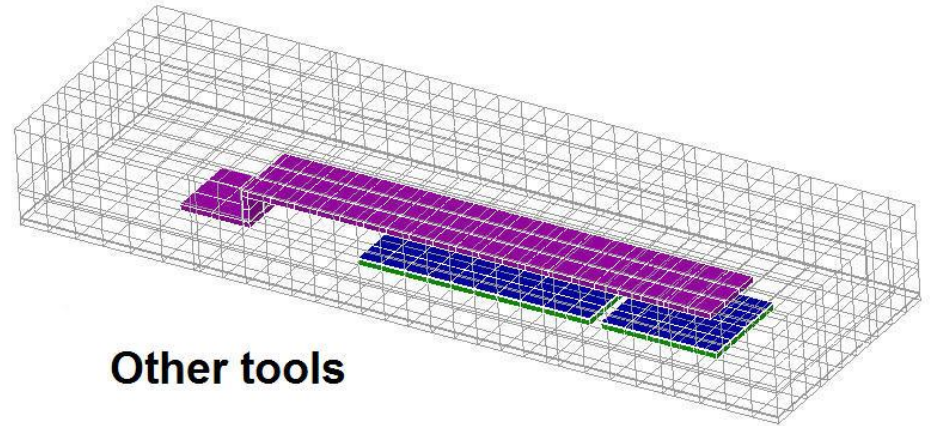
Piezo-resistance (PZR)
solver for PZR sensors

Coupled Electro-Mechanics with Hybrid FEM/BEM

COVENTOR



CoventorWare



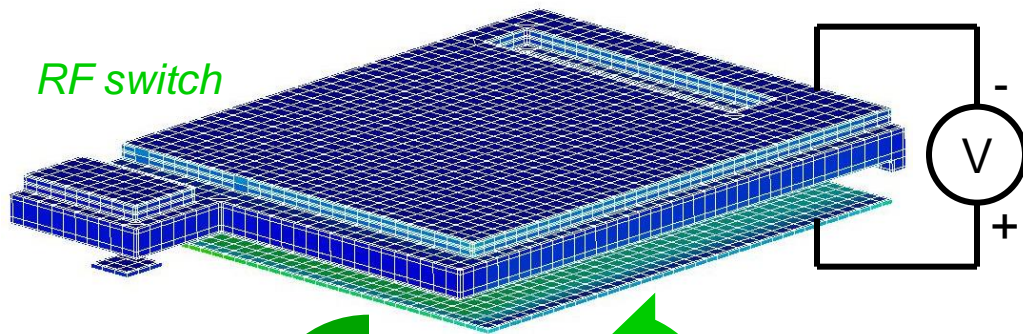
Other tools

- No mesh required in “air” around moving parts
 - Smaller mesh, faster solutions
 - No need to morph mesh as part moves, especially challenging if gap closes
- Fully captures 3D electrostatic fringing fields that others neglect, critical for derived quantities such as
 - Electrostatic force
 - Pull-in / Lift-off voltage
 - Electrostatic spring softening effect

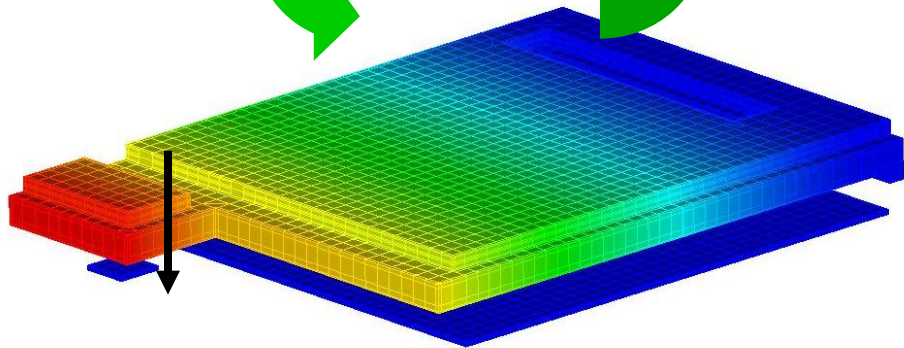
Coupled Electro-Mechanics with Hybrid FEM/BEM (cont'd)

COVENTOR

BEM solver for electrostatic force due to bias voltage
-- uses surface mesh

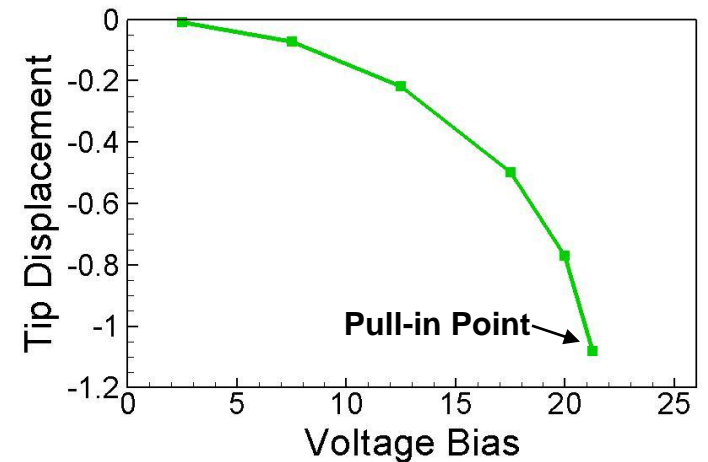


Repeat until
convergence



FEM solver for solid mechanics displacement
-- uses volume mesh

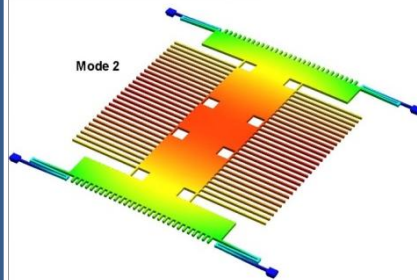
"Pull-in" Result
-- find last stable voltage



Simulation Capabilities for Wide Range of MEMS

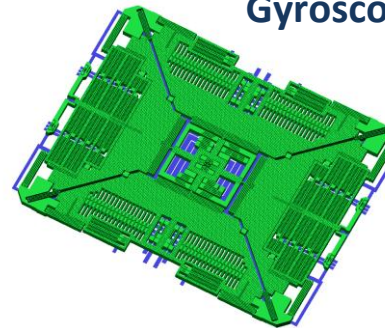
COVENTOR

Accelerometers



- Modal analysis
- Freq. response
- Output capacitance
- Pre-stress effects
- Zero-offset from package effects
- Gas damping

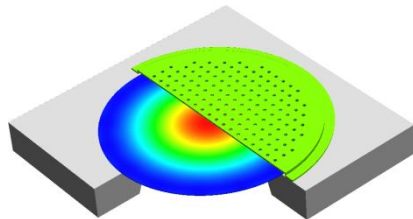
Gyroscopes



Based on ChipWorks teardown

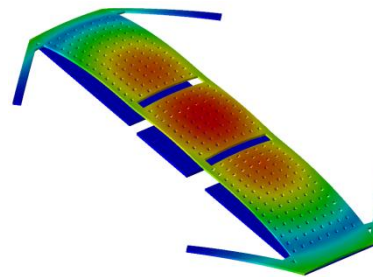
- Pull-in voltage
- Electrostatic drive force
- Output current and capacitance
- Quadrature
- Thermo-elastic damping
- Anchor losses

Microphones



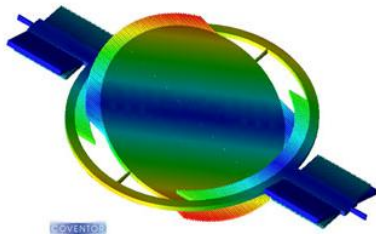
- Freq. response
- Optimize back-plate/membrane perforations
- Electrostatic spring softening
- Pull-in voltage
- Pre-stress

RF Switches & Varactors



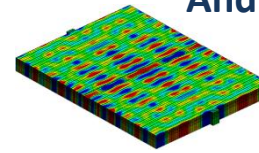
- C-V curve
- Actuation (pull-in) and release (lift-off)
- Closed shape
- Contact force
- Pre-stress effects
- High stress areas
- Shock response

Micro-mirrors

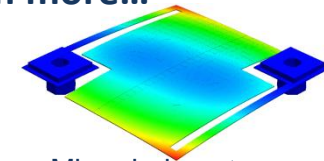


- Analog (scanning): electro-static drive force & response
- Digital display: Actuation (pull-in) and release (lift-off)
- Modal analysis
- Hinge stress
- Gas damping

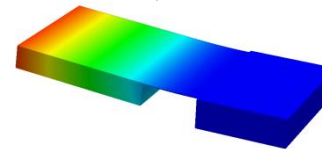
And much more...



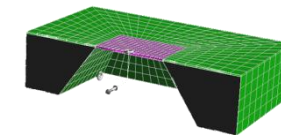
Piezo-MEMS (PZE)



Micro-bolometers



Energy harvesters



Piezo-resistive (PZR) sensors

- “FastPZE”, a new scripted solution for fast analysis of piezoelectric bulk acoustic resonators (FBAR, LVR,...)
 - Usage is covered by a new piezo-resonator tutorial
- Other new tutorials
 - Micro-mirror tutorial now includes Stokes solver for gas damping
 - All-new microbolometer tutorial
- Numerous minor enhancements and bug fixes in Console, Preprocessor and MemMech
- RHEL 6 is supported (available as update for CoventorWare 2014)

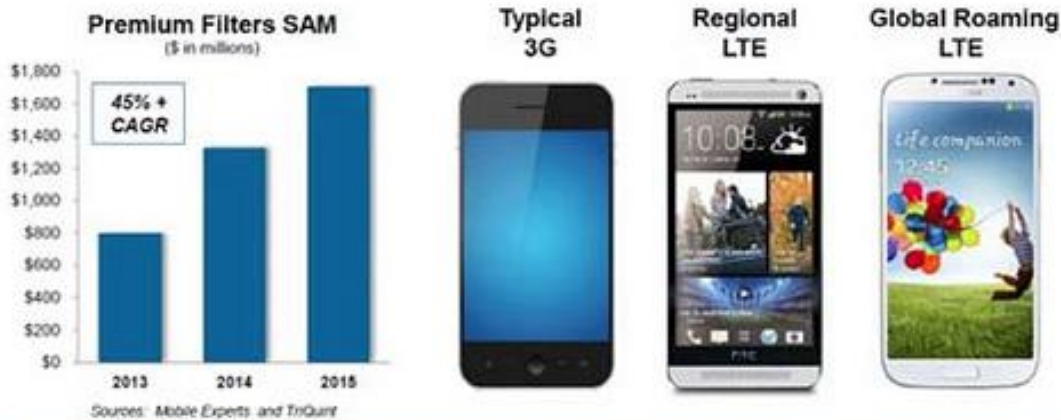
Released in February, 2015

Motivation for FastPZE: RF Filters Need “MEMS”



Exhibit 12

Filter content in different segments of smartphones



	Typical 3G	Regional LTE	Global Roaming LTE
SAW Filters	\$1.25	\$2.25	\$3.00
BAW Filters	\$0.00	\$1.25	\$3.50
Power Amplifiers	\$1.25	\$1.75	\$2.00
Switches / ASMs	\$0.75	\$0.75	\$1.00
Wi-Fi	\$0.50	\$1.00	\$1.00
Total RF Content	\$3.75	\$7.00	\$10.50 +

Source: TriQuint Semiconductor, Morgan Stanley Research

BAW filters are “MEMS-like”, but not our typical customers

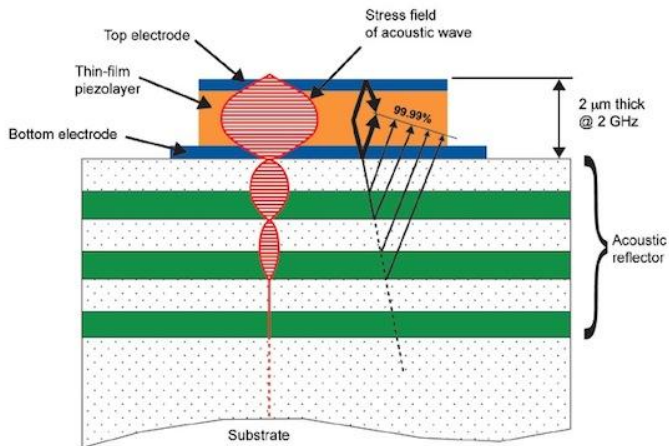
They use **piezoelectric** materials to make mechanical filters for RF signals

The mechanical filter is an **acoustic** resonance (the “A” in BAW and SAW)

<http://blogs.barrons.com/techtraderdaily/2013/11/25/avago-rf-filter-biz-to-benefit-from-cheap-smartphone-growth-says-morgan-stanley/>

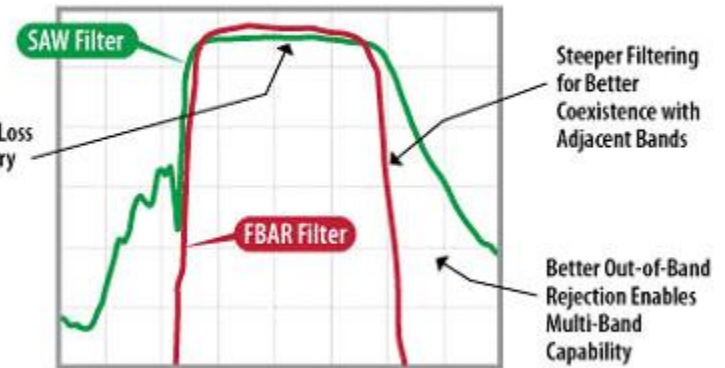
Common Types of BAW Resonators

Thin-Film Bulk Acoustic Resonators (FBARs)



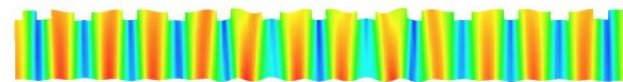
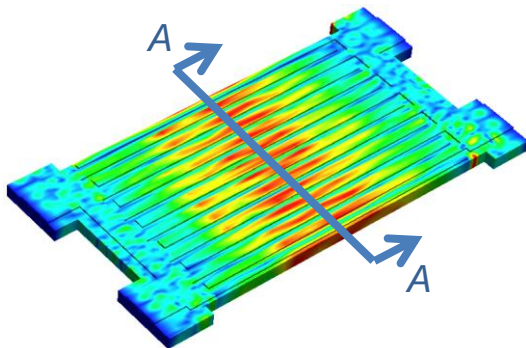
<http://www.edn.com/design/wireless-networking/4413442/SAW--BAW-and-the-future-of-wireless>

FBAR Filter Advantages



http://www.avagotech.com/pages/en/rf_microwave/fbar_filters/

Laterally Vibrating Resonators (LVRs)



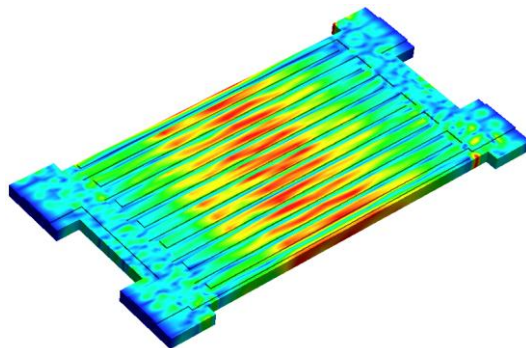
Modal displacement at A-A

LVR advantage: peak frequency is determined by lithography, not thin-film process as in FBARs

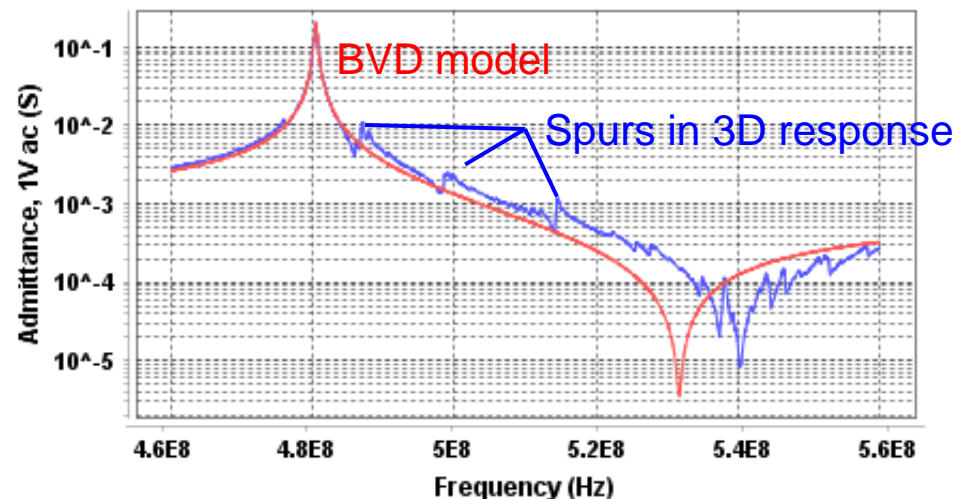
The FastPZE fast-frequency-sweep algorithm is **unique in the industry**

- Up to 30X faster than competing tools (a couple hours vs. days), allows analyzing many designs in **one day instead of weeks**
- Includes **automated multiport filter analysis**: setup and post processing
 - Displays frequency response plots: admittance, charge and S parameters
 - Exports S parameters in Touchstone format (for ADS and other RF simulators)
 - Computes BVD model parameters

New Piezoelectric Resonator tutorial fully explains this new capability



Peak response mode of LVR



FastPZE vs. Conventional Simulation Performance

No. of Mesh Nodes	DoF	No. of Frequencies	Simulation Time	
			Conventional Frequency Sweep (estimated)	FastPZE Fast Frequency Sweep
~18k	67k	1680	<i>~ 7 hrs</i>	15 min
~90k	350k	1900	<i>~74 hrs</i>	2 hrs 20 min

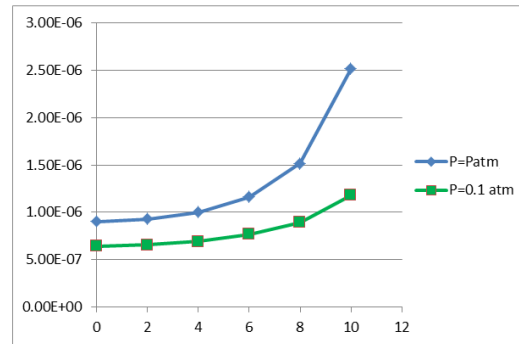
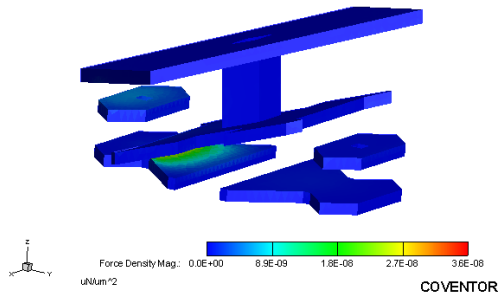
~30X faster!

Type of mesh: Parabolic hex

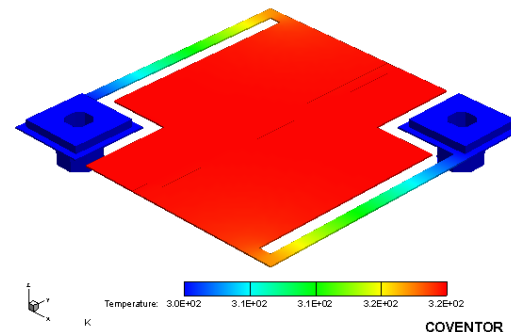
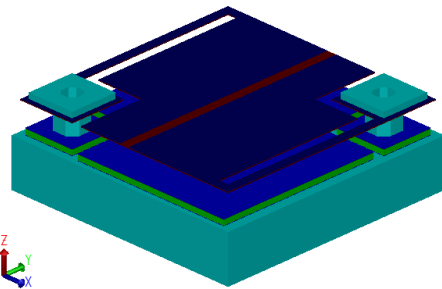
Frequency range: 0.4GHz to 0.6GHz

CPU info: 2.7 GHz, 8 cores

Display Mirror tutorial has added section on gas damping with the Stokes solver in DampingMM



Microbolometer tutorial is completely new, based on a typical device design and covers simulation of key design parameters



Supported Platforms = Operating Systems

Supported “desktop” platforms, 64-bit only

- Windows 7 Pro 64-bit
- Windows 8.1 64-bit
- Red Hat Enterprise Linux Desktop 5
- Red Hat Enterprise Linux Desktop 6

} *Support multiple users
and remote 3D graphics
via free TurboVNC*

The following previously supported platforms are not supported

- Windows XP Pro 32-bit
- Windows XP 64
- Windows 7 Pro 32-bit
- Red Hat Enterprise Linux Workstation 4

The leading MEMS design solution just got better, *again*

Proven success at MEMS leaders worldwide